



SPN6562

Dual N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN6562 is the Dual N-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

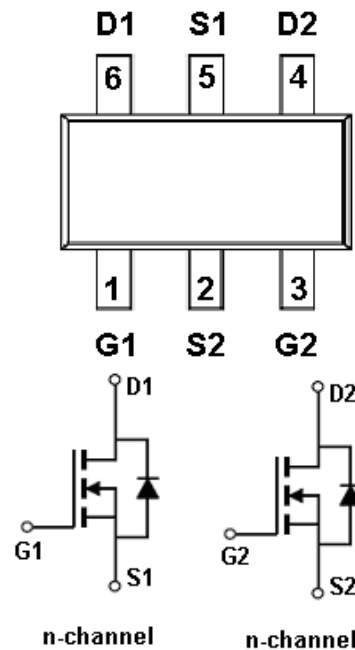
FEATURES

- ◆ N-Channel
30V/2.8A, $R_{DS(ON)}=65m\Omega@V_{GS}=10V$
30V/2.3A, $R_{DS(ON)}=75m\Omega@V_{GS}=4.5V$
30V/1.5A, $R_{DS(ON)}=105m\Omega@V_{GS}=2.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-23-6L package design

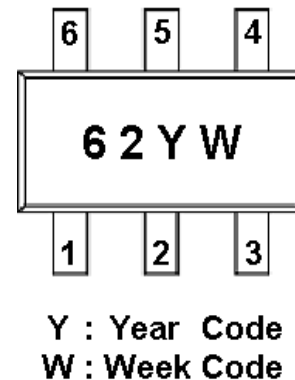
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOT-23-6L)



PART MARKING





SPN6562

Dual N-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	G1	Gate 1
2	S2	Source 2
3	G2	Gate 2
4	D2	Drain 2
5	S1	Source 1
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN6562S26RGB	SOT-23-6L	62

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)

※ SPN6562S26RGB : Tape Reel ; Pb – Free; Halogen - Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	2.8
		TA=70°C	2.3
Pulsed Drain Current	I _{DM}	10	A
Continuous Source Current(Diode Conduction)	I _S	1.25	A
Power Dissipation	P _D	TA=25°C	1.15
		TA=70°C	0.75
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	T ≤ 10sec	50
		Steady State	100



SPN6562

Dual N-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

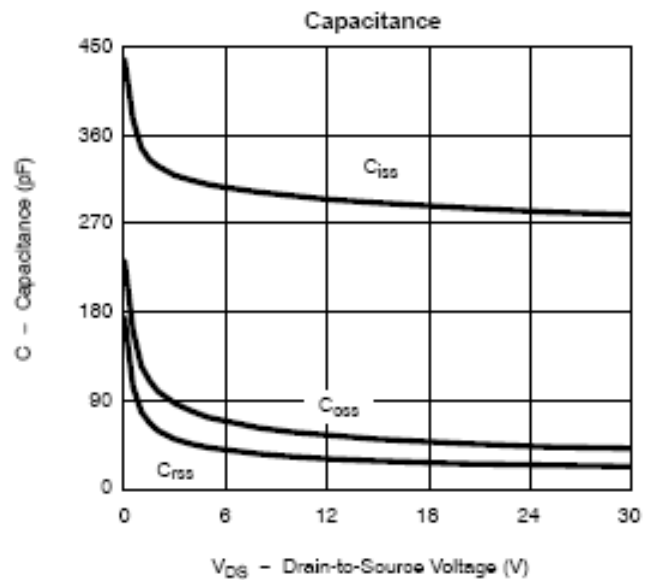
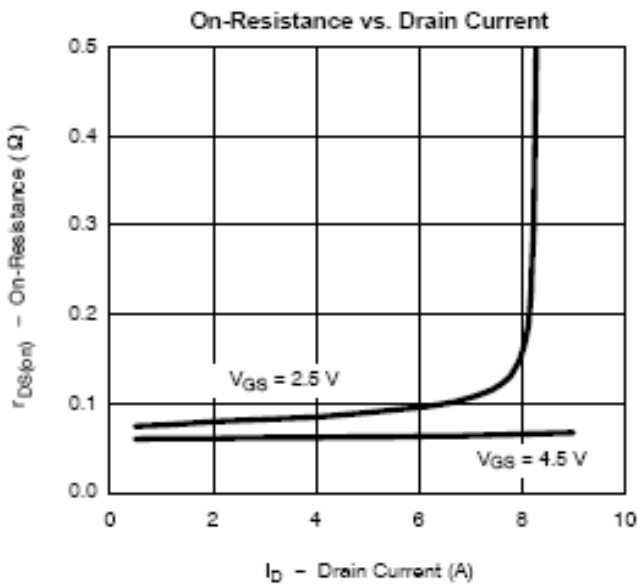
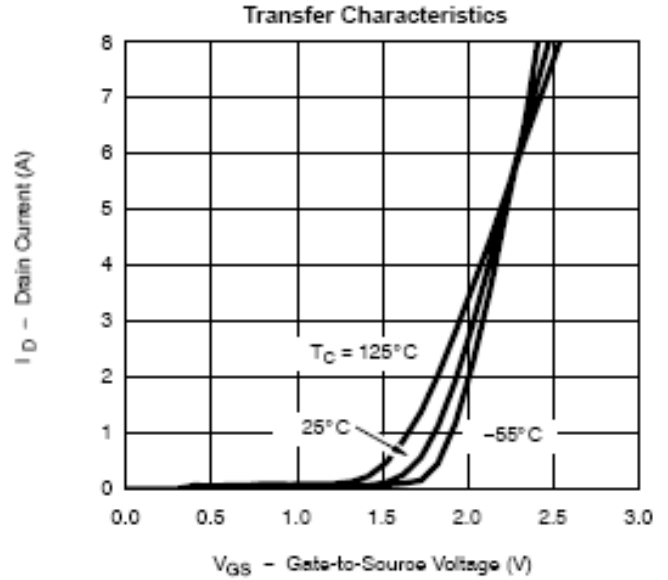
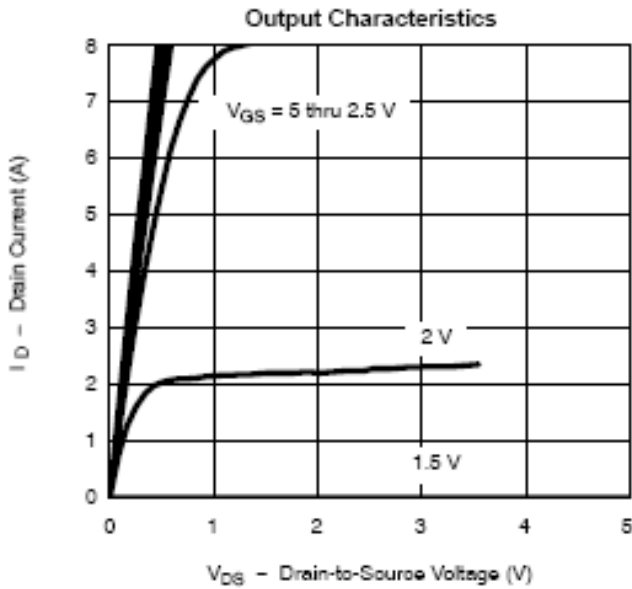
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5		1.6		
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=1.0V$			1	uA	
		$V_{DS}=24V, V_{GS}=0.0V$ $T_J=55^\circ C$			10		
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 4.5V, V_{GS}=10V$	6			A	
		$V_{DS} \geq 4.5V, V_{GS}=4.5V$	4				
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D=2.8A$		0.055	0.065	Ω	
		$V_{GS} = 4.5V, I_D=2.3A$		0.065	0.075		
		$V_{GS} = 2.5V, I_D=1.5A$		0.085	0.105		
Forward Transconductance	g_{fs}	$V_{DS}=4.5V, I_D=2.5A$		4.6		S	
Diode Forward Voltage	V_{SD}	$I_S=1.25A, V_{GS}=0V$		0.82	1.2	V	
Dynamic							
Total Gate Charge	Q_g	$V_{DS}=15, V_{GS}=4.5V$ $I_D=2.0A$		4.2	6	nC	
Gate-Source Charge	Q_{gs}			0.6			
Gate-Drain Charge	Q_{gd}			1.5			
Input Capacitance	C_{iss}	$V_{DS}=15, V_{GS}=0V$ $f = 1MHz$		350		pF	
Output Capacitance	C_{oss}			55			
Reverse Transfer Capacitance	C_{rss}			41			
Turn-On Time	$t_{d(on)}$	$V_{DD}=15, R_L=10\Omega$ $V_{GEN}=10V, R_G=3\Omega$		2.5		nS	
	t_r			2.5			
Turn-Off Time	$t_{d(off)}$				20		
	t_f				4		



SPN6562

Dual N-Channel Enhancement Mode MOSFET

TYPICAL CHARACTERISTICS

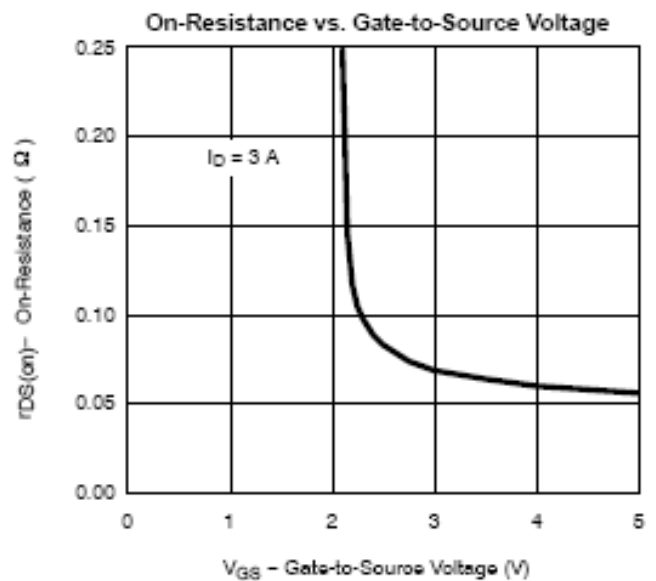
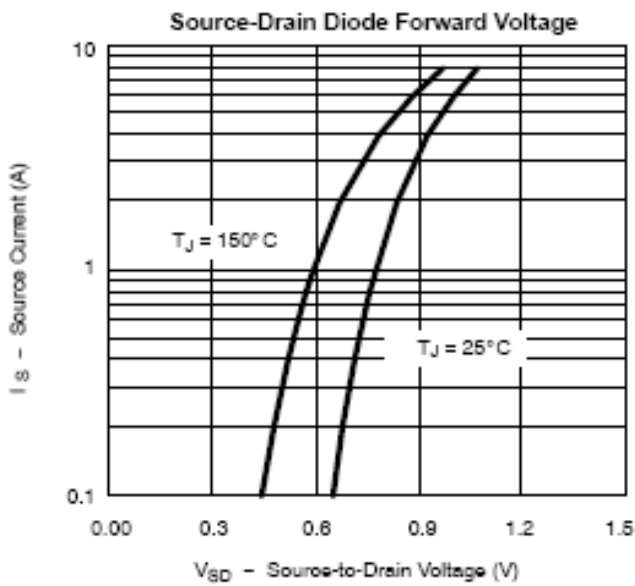
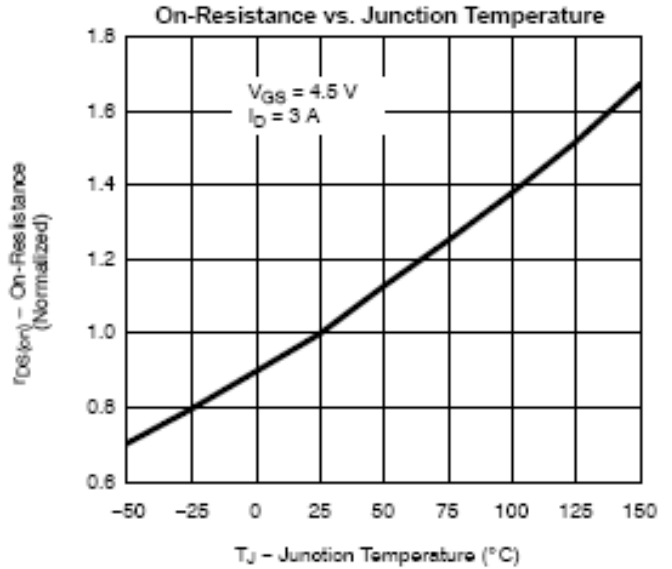
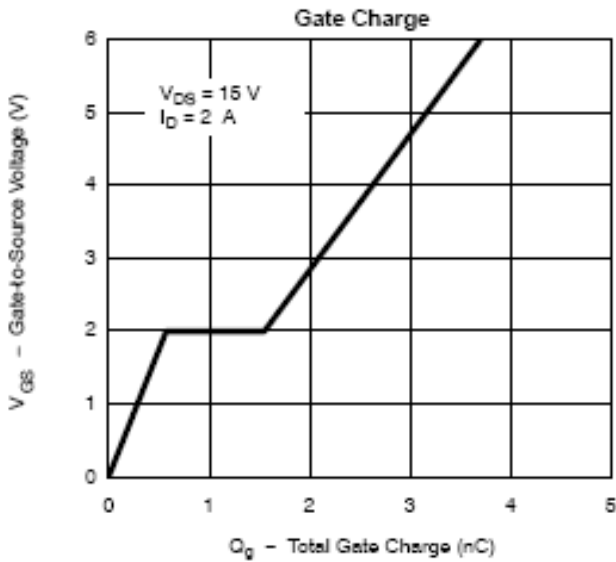




SPN6562

Dual N-Channel Enhancement Mode MOSFET

TYPICAL CHARACTERISTICS

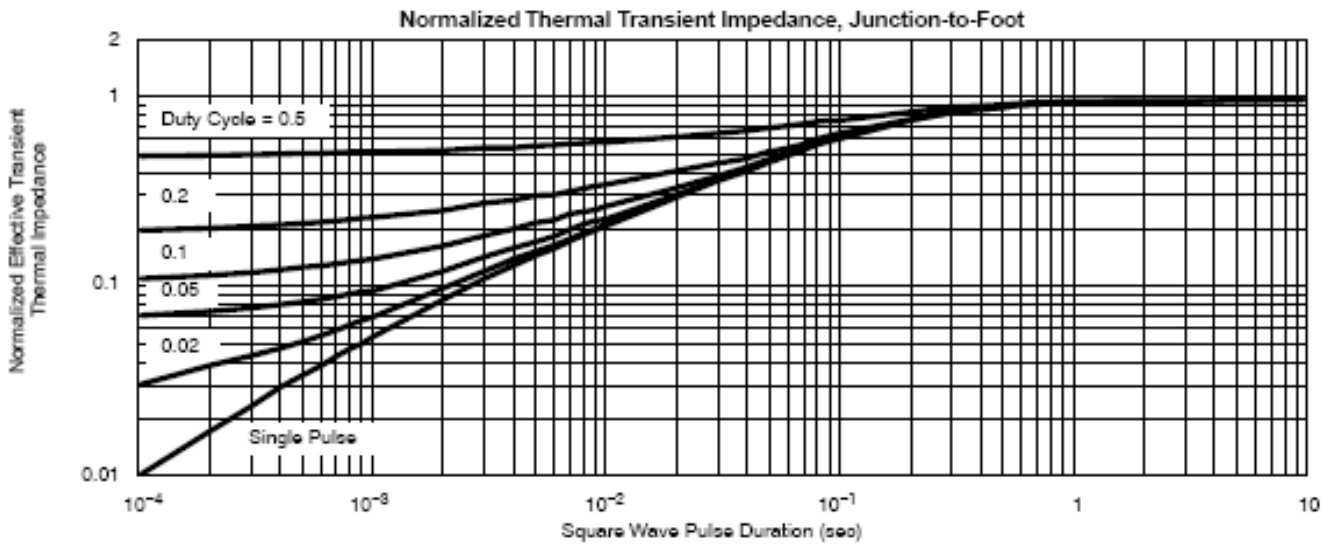
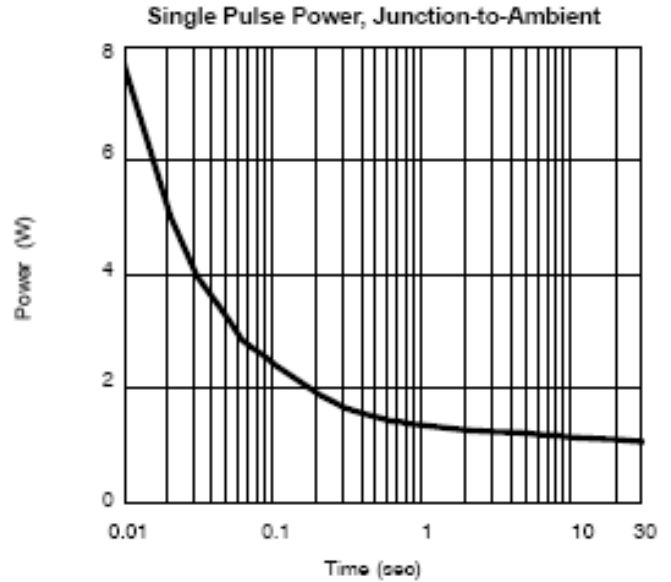
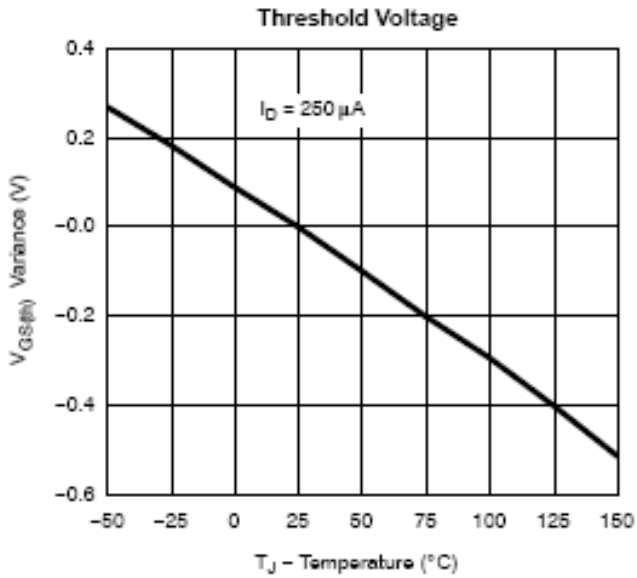




SPN6562

Dual N-Channel Enhancement Mode MOSFET

TYPICAL CHARACTERISTICS





SPN6562

Dual N-Channel Enhancement Mode MOSFET

Information provided is alleged to be exact and consistent. SYNC Power Corporation presumes no responsibility for the penalties of use of such information or for any violation of patents or other rights of third parties which may result from its use. No license is granted by allegation or otherwise under any patent or patent rights of SYNC Power Corporation. Conditions mentioned in this publication are subject to change without notice. This publication surpasses and replaces all information previously supplied. SYNC Power Corporation products are not authorized for use as critical components in life support devices or systems without express written approval of SYNC Power Corporation.

© The SYNC Power logo is a registered trademark of SYNC Power Corporation

© 2021 SYNC Power Corporation – Printed in Taiwan – All Rights Reserved

SYNC Power Corporation

7F-2, No.3-1, Park Street

NanKang District (NKSP), Taipei, Taiwan 115

Phone: 886-2-2655-8178

Fax: 886-2-2655-8468

© <http://www.syncpower.com>